

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

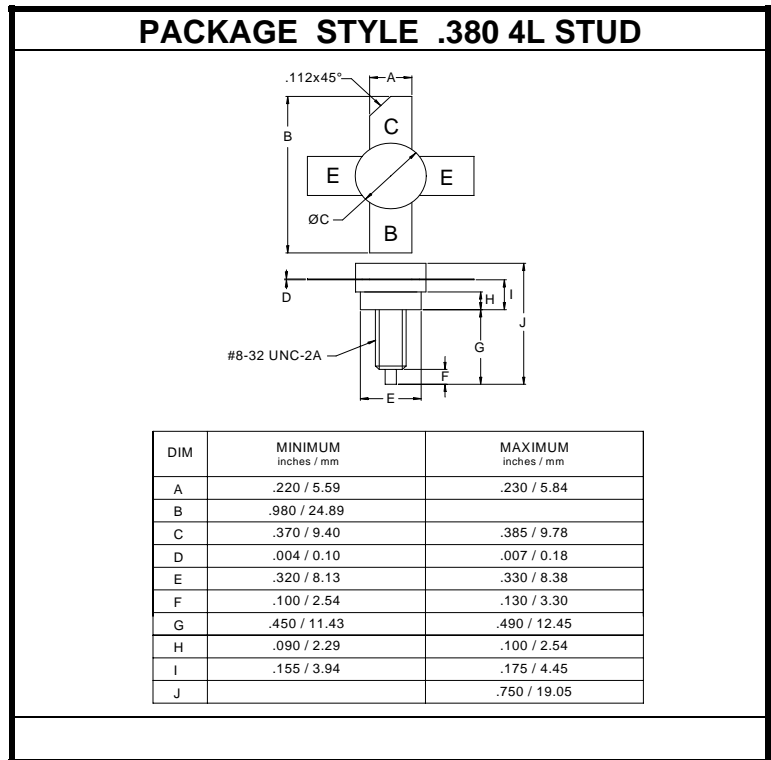
The **ASI BLW31** is an NPN silicon power transistor, designed 175 MHz applications, especially suited for design of wide-band and semi-wide-band VHF amplifiers.

FEATURES:

- Common Emitter-Class-A, B or C
- $P_G = 9$ dB at 28 W/175 MHz
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	6.0 A
V_{CESM}	36 V
V_{CEO}	18 V
V_{EBO}	4.0 V
P_{DISS}	96 W @ $T_{MB} = 25$ °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	1.85 °C/W



CHARACTERISTICS $T_C = 25$ °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 100$ mA	18			V
BV_{CES}	$I_C = 25$ mA	36			V
BV_{EBO}	$I_E = 10$ mA	4.0			V
I_{CES}	$V_{CE} = 18$ V			10	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 3.5$ A	10		80	---
C_{CC} C_{RE} C_{CS}	$V_{CB} = 13.5$ V $f = 1.0$ MHz		92 58 2		pF
P_G η_C	$V_{CC} = 13.5$ V $P_{OUT} = 28$ W $f = 175$ MHz	9.0 60	9.5 70		dB %